

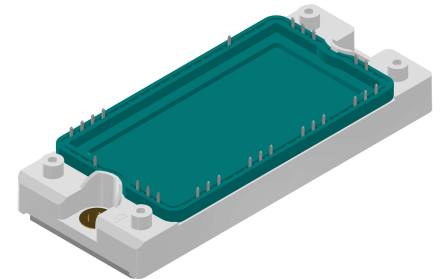
# Standard Rectifier Module

3~ Rectifier	Brake Chopper
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{DAV} = 240 \text{ A}$	$I_{C25} = 180 \text{ A}$
$I_{FSM} = 1500 \text{ A}$	$V_{CE(sat)} = 1.7 \text{ V}$

## 3~ Rectifier Bridge + Brake Unit

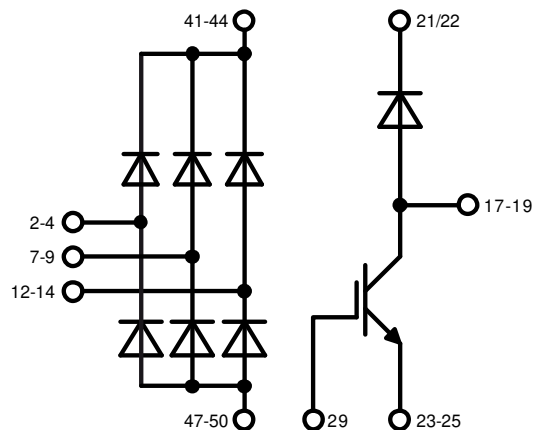
Part number

**MDMA240UB1600ED**



Backside: isolated

 E72873



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current
- X2PT - 2nd generation Xtreme light Punch Through
- Rugged X2PT design results in:
  - short circuit rated for 10  $\mu\text{sec}$ .
  - very low gate charge
  - low EMI
  - square RBSOA @ 2x  $I_c$
- Thin wafer technology combined with X2PT design results in a competitive low  $V_{CE(sat)}$  and low thermal resistance

### Applications:

- 3~ Rectifier with brake unit for drive inverters

### Package: E2-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Disclaimer Notice

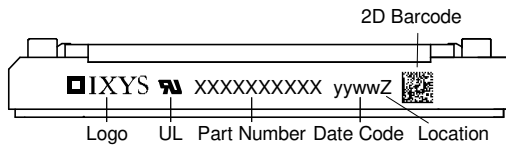
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		1700	V
$V_{RRM}$	max. repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		1600	V
$I_R$	reverse current	$V_R = 1600$ V		$T_{VJ} = 25^{\circ}C$		100	$\mu A$
		$V_R = 1600$ V		$T_{VJ} = 150^{\circ}C$		2	mA
$V_F$	forward voltage drop	$I_F = 80$ A		$T_{VJ} = 25^{\circ}C$		1.28	V
		$I_F = 240$ A				1.92	V
		$I_F = 80$ A		$T_{VJ} = 125^{\circ}C$		1.22	V
		$I_F = 240$ A				2.02	V
$I_{DAV}$	bridge output current	$T_C = 85^{\circ}C$		$T_{VJ} = 150^{\circ}C$		240	A
		rectangular	$d = 120^{\circ}$				
$V_{FO}$	threshold voltage			$T_{VJ} = 150^{\circ}C$		0.80	V
$r_F$	slope resistance					5.2	m $\Omega$
						} for power loss calculation only	
$R_{thJC}$	thermal resistance junction to case					0.4	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.1		K/W
$P_{tot}$	total power dissipation			$T_C = 25^{\circ}C$		312	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^{\circ}C$		1.50	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.62	kA
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^{\circ}C$		1.28	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.38	kA
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^{\circ}C$		11.3	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		10.9	kA <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^{\circ}C$		8.13	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		7.87	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^{\circ}C$		58	pF

Brake IGBT + Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{CES}$	collector emitter voltage				1200	V	
$V_{GES}$	max. DC gate voltage				$\pm 20$	V	
$V_{GEM}$	max. transient gate emitter voltage				$\pm 30$	V	
$I_{C25}$	collector current				180	A	
$I_{C80}$					140	A	
$P_{tot}$	total power dissipation				500	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 100 \text{ A}; V_{GE} = 15 \text{ V}$			1.7	V	
					1.9	V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 4 \text{ mA}; V_{GE} = V_{CE}$	6	6.8	7.5	V	
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}$			0.1	mA	
					0.1	mA	
$I_{GES}$	gate emitter leakage current	$V_{GE} = \pm 20 \text{ V}$			500	nA	
$Q_{G(on)}$	total gate charge	$V_{CE} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 100 \text{ A}$		340		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600 \text{ V}; I_C = 100 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 6.8 \Omega$		230		ns	
$t_r$	current rise time			70		ns	
$t_{d(off)}$	turn-off delay time			380		ns	
$t_f$	current fall time			230		ns	
$E_{on}$	turn-on energy per pulse			12.5		mJ	
$E_{off}$	turn-off energy per pulse			11.5		mJ	
<b>RBSOA</b>	reverse bias safe operating area	$V_{GE} = \pm 15 \text{ V}; R_G = 6.8 \Omega$					
$I_{CM}$		$V_{CEK} = 1200 \text{ V}$			300	A	
<b>SCSOA</b>	short circuit safe operating area	$V_{CEK} = 1200 \text{ V}$					
$t_{SC}$	short circuit duration	$V_{CE} = 720 \text{ V}; V_{GE} = \pm 15$			10	$\mu\text{s}$	
$I_{SC}$	short circuit current	$R_G = 6.8 \Omega$ ; non-repetitive		450		A	
$R_{thJC}$	thermal resistance junction to case				0.25	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.10		K/W	
<b>Brake Diode</b>							
$V_{RRM}$	max. repetitive reverse voltage				1200	V	
$I_{F25}$	forward current				88	A	
$I_{F80}$					59	A	
$V_F$	forward voltage	$I_F = 60 \text{ A}$			2.20	V	
					1.95	V	
$I_R$	reverse current	$V_R = V_{RRM}$			0.1	mA	
					1.2	mA	
$Q_{rr}$	reverse recovery charge	$V_R = 600 \text{ V}$ $-di_f/dt = 900 \text{ A}/\mu\text{s}$ $I_F = 60 \text{ A}; V_{GE} = 0 \text{ V}$		9.6		$\mu\text{C}$	
$I_{RM}$	max. reverse recovery current			47		A	
$t_{rr}$	reverse recovery time			450		ns	
$E_{rec}$	reverse recovery energy			3		mJ	
$R_{thJC}$	thermal resistance junction to case				0.6	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.1		K/W	



Package E2-Pack		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			50	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				176		g
$M_D$	mounting torque		3		6	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



**Part description**

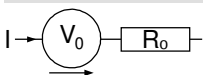
- M = Module
- D = Diode
- M = Standard Rectifier
- A = (up to 1800V)
- 240 = Current Rating [A]
- UB = 3- Rectifier Bridge + Brake Unit
- 1600 = Reverse Voltage [V]
- ED = E2-Pack

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA240UB1600ED	MDMA240UB1600ED	Box	6	520461

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150^{\circ}C$

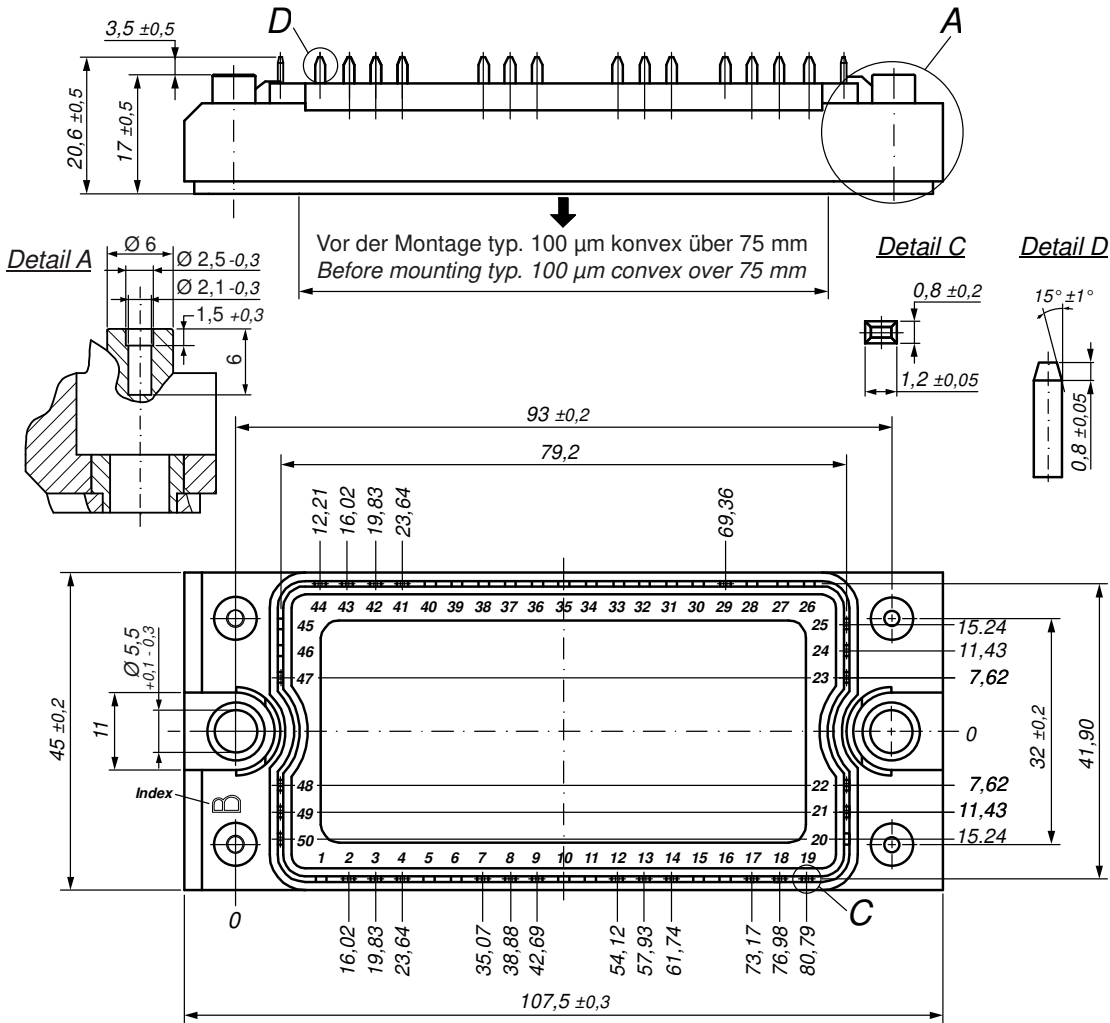


**Rectifier**

$V_{0\ max}$	threshold voltage	0.8	V
$R_{0\ max}$	slope resistance *	2.1	mΩ



**Outlines E2-Pack**

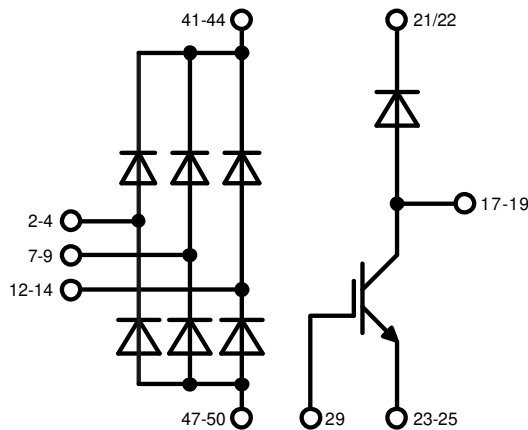


**Bemerkung / Note:**

- Nichttolerierete Maße nach / Measure without tolerances according DIN ISO 2768-T1-m
- PCB-Lochmuster / PCB hole pattern: **see pin position**
- Toleranz Pin-Position und PCB-Lochmuster / Tolerance of pin position and PCB hole pattern:  $\oplus 0.1$
- Montageanleitung / Mounting instruction: [www.ixys.com](http://www.ixys.com) **Application note IXAN0024**

**Detail A:** PCB-Montage / Mounting on PCB <sup>L</sup>

- Empfohlene, selbstschneidende Schraube / Recommended, self-tapping screw: **EJOT PT®** (Größe / size: **K25**) <sup>L</sup>
- Max. Schraubenlänge / Max. screw length: **PCB-Dicke / thickness + 6 mm** (max. Lochtiefe / hole depth) <sup>L</sup>
- Empfohlenes Drehmoment / Recommended mounting torque: **1.5 Nm**



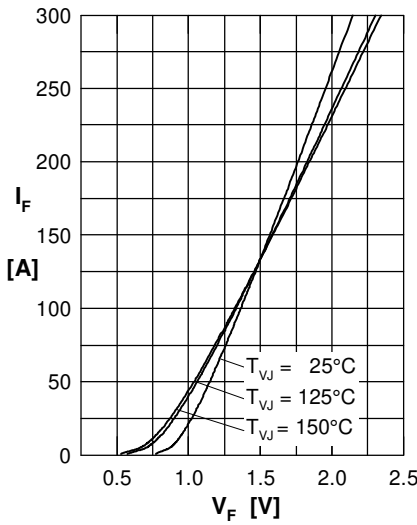
**Rectifier**


Fig. 1 Forward current versus voltage drop per diode

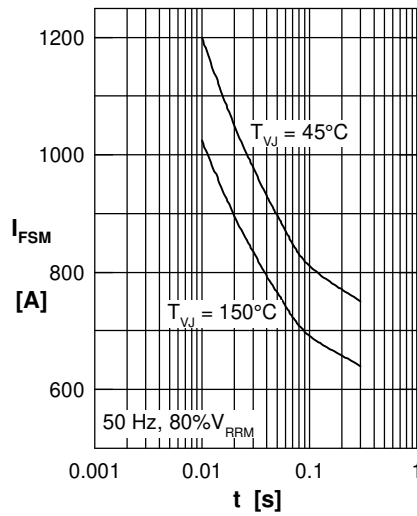


Fig. 2 Surge overload current vs. time per diode

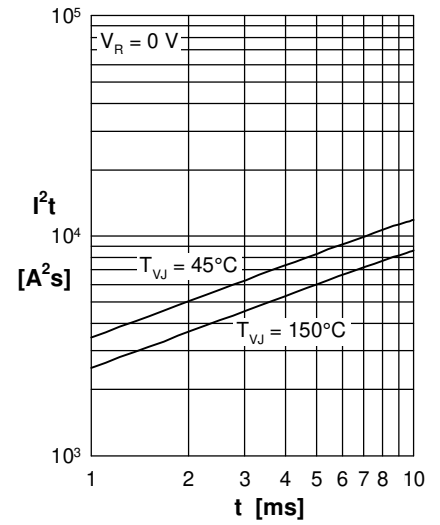
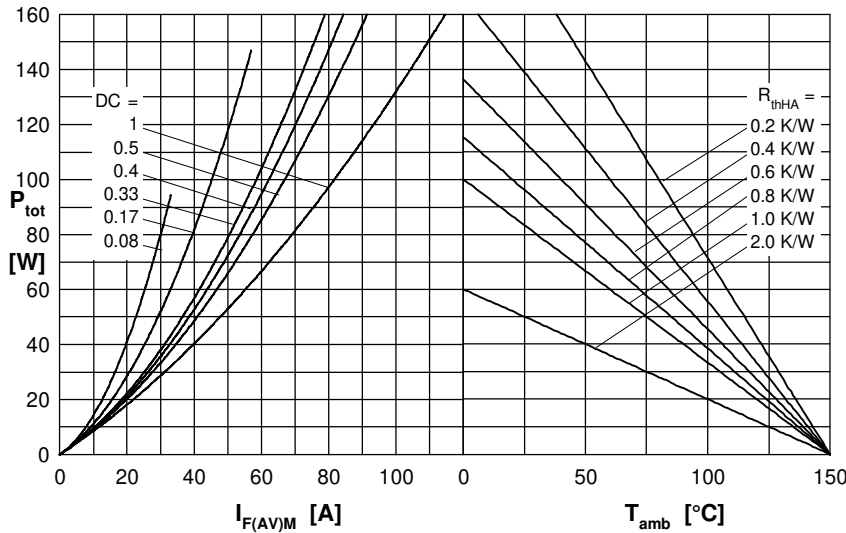

 Fig. 3  $I^2t$  versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

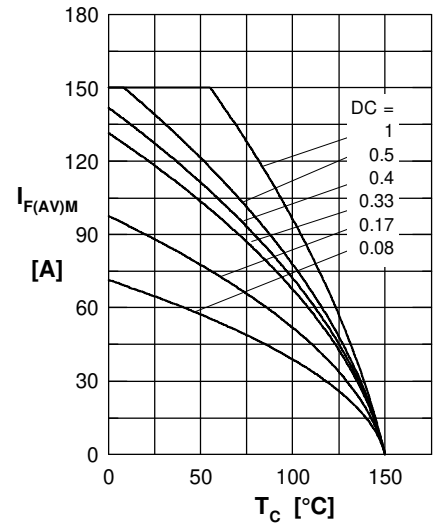


Fig. 5 Max. forward current vs. case temperature per diode

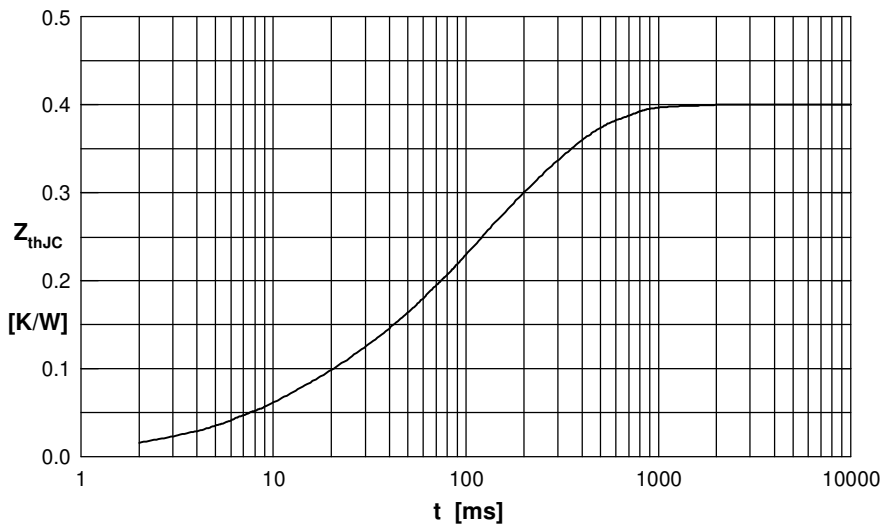


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.050	0.010
2	0.003	0.007
3	0.090	0.055
4	0.187	0.250
5	0.070	0.120

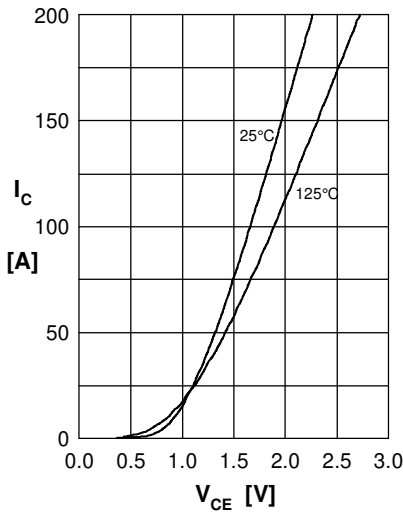
**Brake IGBT + Diode**


Fig.1 Output characteristics IGBT



Fig.2 Typ. output characteristics IGBT

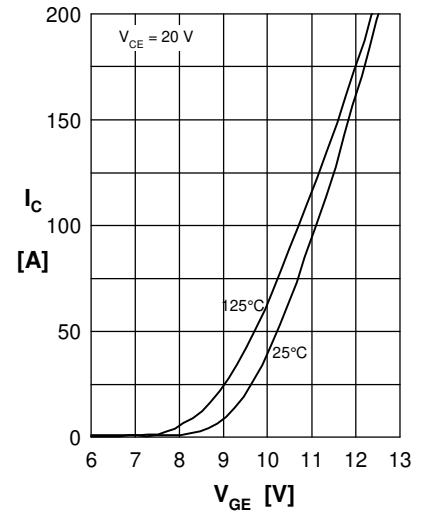


Fig.3 Typ. transfer charact. IGBT

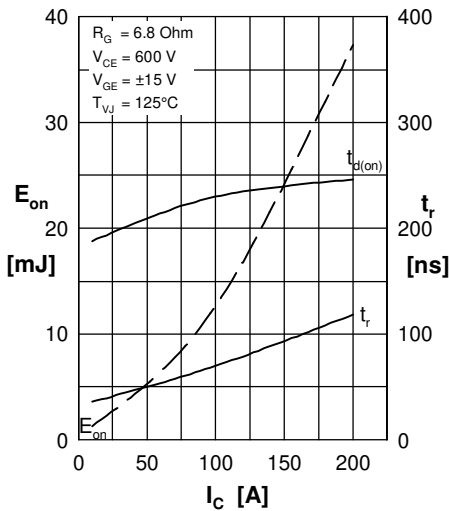


Fig.4 Typ. turn-on energy &amp; switch. times vs. collector current

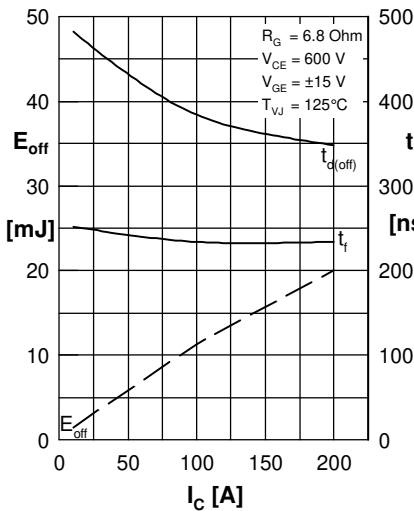


Fig.5 Typ. turn-off energy &amp; switch. times vs. collector current

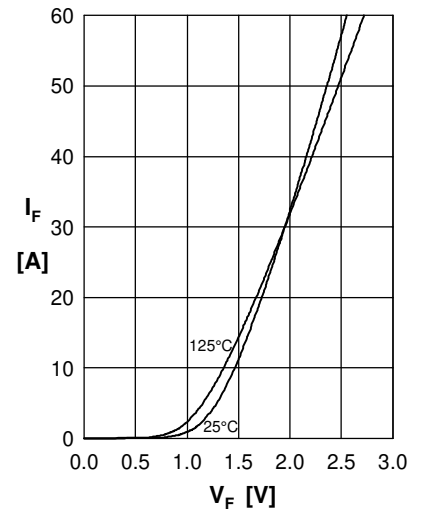
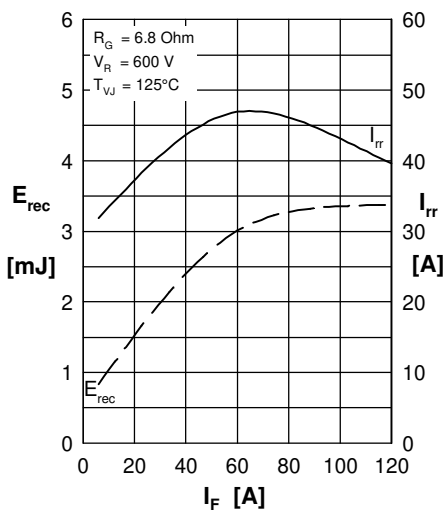

 Fig.6 Typ. forward current versus  $V_F$ 


Fig.7 Typ. reverse recovery characteristics Diode

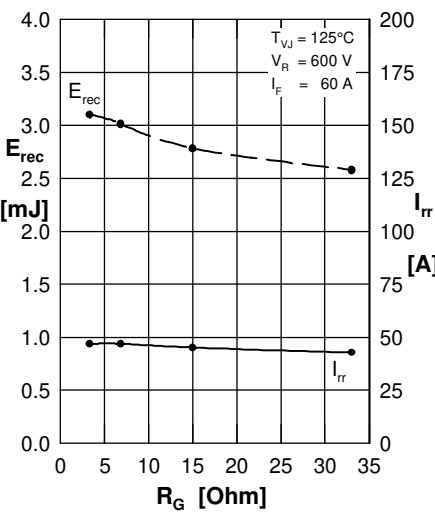


Fig.8 Typ. reverse recovery characteristics Diode

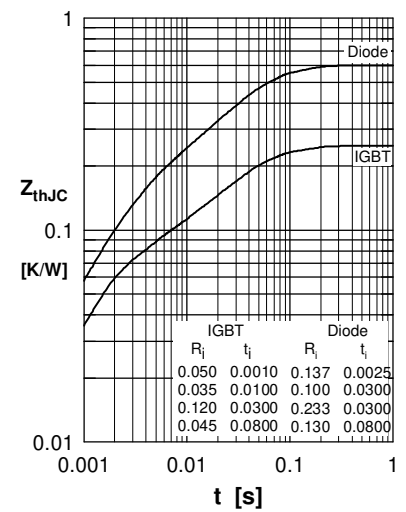


Fig.9 Transient thermal resistance junction to case